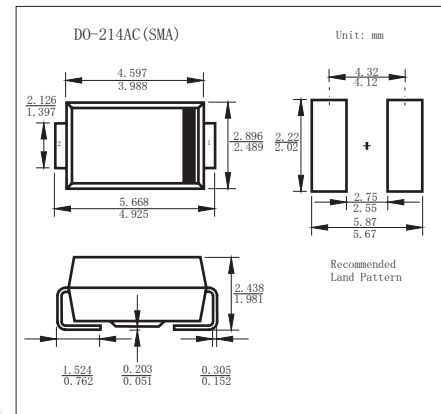


Schottky Diodes

1N5817 ~ 1N5819

■ Features

- Low profile package
- Ideal for automated placement
- Guardring for overvoltage protection
- Low power losses, high efficiency
- Low forward voltage drop
- High surge capability



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	1N5817	1N5818	1N5819	Unit
Peak Repetitive Peak Reverse Voltage	VRRM	20	30	40	V
RMS Reverse Voltage	VR(RMS)	14	21	28	
DC Blocking Voltage	VR	20	30	40	
Average Rectified Rectified Current	IFAV	1			A
Peak Forward Surge Current @=8.3ms	IFSM	40			
Thermal Resistance Junction to Ambient (Note.1)	RθJA	88			°C/W
Thermal Resistance Junction to Lead (Note.1)	RθJL	28			
Voltage Rate of Change (rated VR)	dv/dt	10000			V/us
Junction Temperature	TJ	-60 to 125			°C
Storage Temperature range	Tstg	-65 to 150			

Note.1: P.C.B. mounted with 0.2 x 0.2" (5.0 x 5.0 mm) copper pad areas

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage (Note.1)	VF	IF= 1 A			0.5	V
Reverse voltage leakage current(Note.1)	IR	Ta = 25°C			0.2	mA
		Ta = 100°C			6	

Note.1: Pulse test: 300 μs pulse width, 1 % duty cycle

■ Marking

NO.	1N5817	1N5818	1N5819
Marking	SS12	SS13	SS14

Schottky Diodes

1N5817 ~ 1N5819

Typical Characteristics

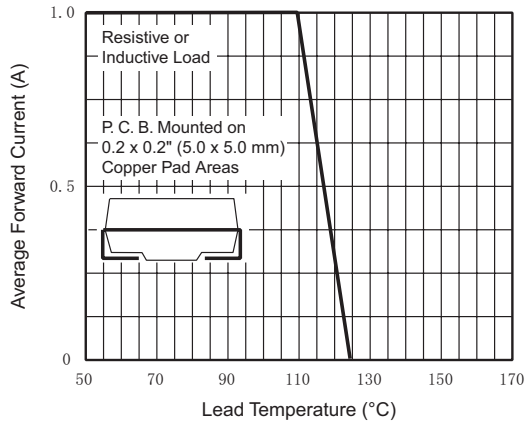


Figure 1. Forward Current Derating Curve

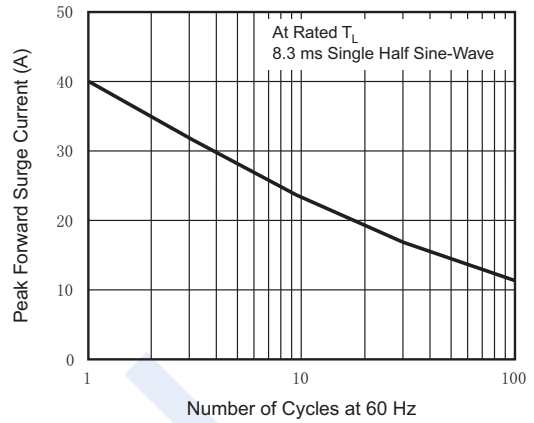


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current

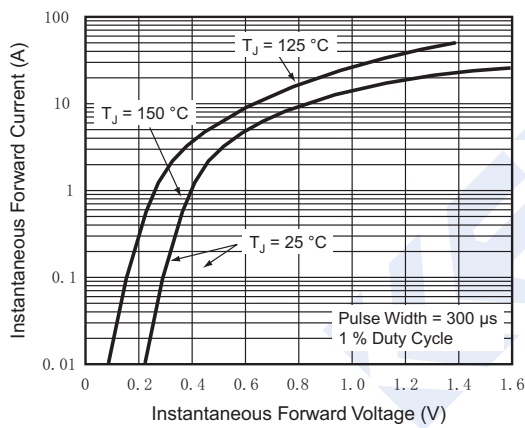


Figure 3. Typical Instantaneous Forward Characteristics

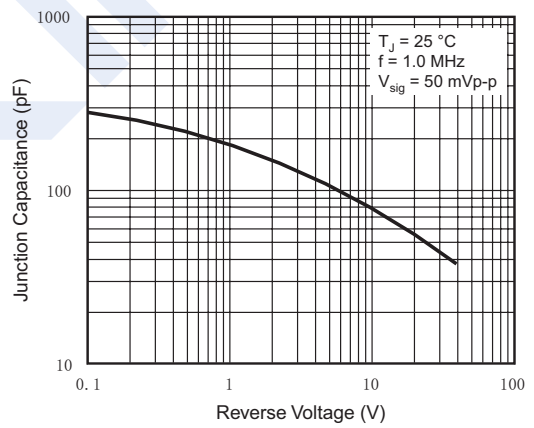


Figure 5. Typical Junction Capacitance

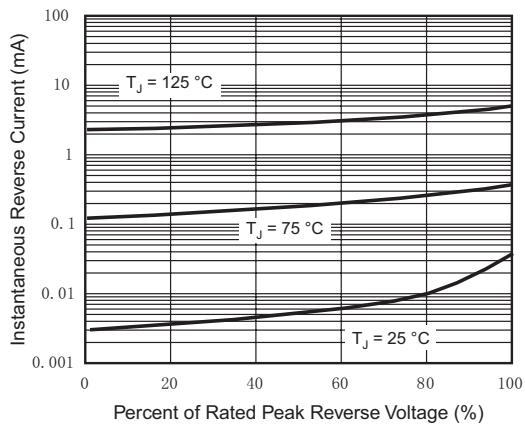


Figure 4. Typical Reverse Characteristics